

Title (en)
LOW-CAPACITY VERTICAL DIODE

Title (de)
VERTIKALE DIODE MIT SCHWACHER KAPAZITÄT

Title (fr)
DIODE VERTICALE DE FAIBLE CAPACITE

Publication
EP 1428264 A1 20040616 (FR)

Application
EP 02783155 A 20020910

Priority
• FR 0203080 W 20020910
• FR 0111680 A 20010910

Abstract (en)
[origin: FR2829616A1] A vertical diode with front face mounting and of low capacity in a semiconductor substrate (1) comprises: (a) a projecting first zone incorporating at least one semiconducting layer (3) doped with a conductivity type opposite to that of the substrate, the upper surface of the semiconducting layer carrying a first solder bead (23); and (b) a second zone incorporating on the substrate a thin conducting track (16) carrying at least two second solder beads (24). The first and second solder beads define a plane parallel to the plane of the substrate. An Independent claim is also included for the formation of a vertical diode with front face mounting and low capacity in a semiconductor substrate.

IPC 1-7
H01L 29/861; **H01L 29/868**

IPC 8 full level
H01L 29/861 (2006.01); **H01L 29/868** (2006.01)

CPC (source: EP US)
H01L 29/8613 (2013.01 - EP US); **H01L 29/868** (2013.01 - EP US); **Y02E 10/548** (2013.01 - EP)

Citation (search report)
See references of WO 03026020A1

Designated contracting state (EPC)
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR IE IT LI LU MC NL PT SE SK TR

DOCDB simple family (publication)
FR 2829616 A1 20030314; **FR 2829616 B1 20040312**; EP 1428264 A1 20040616; US 2004207050 A1 20041021; US 2005242363 A1 20051103; US 6924546 B2 20050802; US 7507620 B2 20090324; WO 03026020 A1 20030327

DOCDB simple family (application)
FR 0111680 A 20010910; EP 02783155 A 20020910; FR 0203080 W 20020910; US 15999105 A 20050623; US 48915304 A 20040310